Final datasheet
EasyPACK™ module with CoolSiC™ Trench MOSFET and PressFIT / NTC / TIM

Features


Typical appearance

- Electrical features
  - V_{DSS} = 1200 V
  - I_{DN} = 100 A / I_{DRM} = 200 A
  - High current density
  - Low switching losses
  - Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder
- Mechanical features
  - Rugged mounting due to integrated mounting clamps
  - Integrated NTC temperature sensor
  - PressFIT contact technology
  - Pre-applied thermal interface material

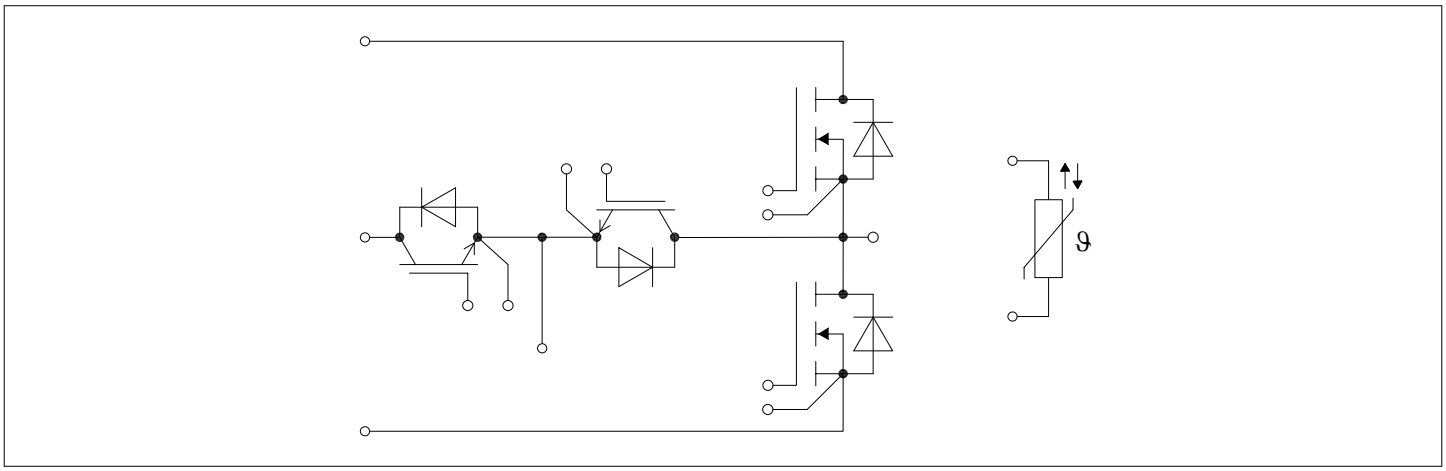
Potential applications

- Solar applications
- Three-level applications
- DC charger for EV

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 60 s	3.0	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, f = 50 Hz, *t* = 60 s	3.0	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	*CTI*		> 200	
Relative thermal index (electrical)	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			12		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_H = 25 °C, per switch		0.4		mΩ
Storage temperature	T_{stg}		-40		125	°C
Maximum baseplate operation temperature	T_{BPmax}				125	°C
Mounting force per clamp	*F*		40		80	N
Weight	*G*			39		g

***Note**: The current under continuous operation is limited to 25 A rms per connector pin.*
Storage and shipment of modules with TIM => see AN2012-07.

2 MOSFET

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Implemented drain current	I_{DN}			100	A
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 65 °C	85	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		200	A
Gate-source voltage, max. transient voltage	V_{GS}	*D* < 0.01		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 100 A	V_{GS} = 18 V, T_{vj} = 25 °C		8.1	12	mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		13.1		
			V_{GS} = 18 V, T_{vj} = 175 °C		17.4		
			V_{GS} = 15 V, T_{vj} = 25 °C		9.7		
Gate threshold voltage	$V_{GS(th)}$	I_D = 40 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V)		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			0.297		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			2.1		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		8.8		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.42		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.028		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			172		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.06	380	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 100 A, R_{Gon} = 11 Ω, V_{DD} = 400 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		42		ns
			T_{vj} = 125 °C		44		
			T_{vj} = 175 °C		48		
Rise time (inductive load)	t_r	I_D = 100 A, R_{Gon} = 11 Ω, V_{DD} = 400 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		27		ns
			T_{vj} = 125 °C		28		
			T_{vj} = 175 °C		28		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 100 A, R_{Goff} = 0.75 Ω, V_{DD} = 400 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		40		ns
			T_{vj} = 125 °C		43		
			T_{vj} = 175 °C		46		
Fall time (inductive load)	t_f	I_D = 100 A, R_{Goff} = 0.75 Ω, V_{DD} = 400 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		11		ns
			T_{vj} = 125 °C		12		
			T_{vj} = 175 °C		13		
Turn-on energy loss per pulse	E_{on}	I_D = 100 A, V_{DD} = 400 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Gon} = 11 Ω, di/dt = 4.48 kA/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		2.25		mJ
			T_{vj} = 125 °C		2.77		
			T_{vj} = 175 °C		3.03		
Turn-off energy loss per pulse	E_{off}	I_D = 100 A, V_{DD} = 400 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Goff} = 0.75 Ω, dv/dt = 39.8 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.32		mJ
			T_{vj} = 125 °C		0.35		
			T_{vj} = 175 °C		0.37		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material				0.581	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.*

$T_{vj,op}$ > 150°C is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13

3 Body diode (MOSFET)

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -3 V	T_H = 65 °C	32	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 100 A, V_{GS} = -3 V	T_{vj} = 25 °C		4.2	5.35	V
			T_{vj} = 125 °C		3.9		
			T_{vj} = 175 °C		3.8		

(table continues...)

Table 7 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Peak reverse recovery current	I_{rrm}	I_{SD} = 100 A, di_s/dt = 1.05 kA/µs, V_{DD} = 400 V, V_{GS}=-3 V	T_{vj} = 25 °C		94		A
			T_{vj} = 125 °C		116		
			T_{vj} = 175 °C		136		
Recovered charge	Q_{rr}	I_{SD} = 100 A, di_s/dt = 1.05 kA/µs, V_{DD} = 400 V, V_{GS}=-3 V	T_{vj} = 25 °C		1.3		µC
			T_{vj} = 125 °C		2.11		
			T_{vj} = 175 °C		2.6		
Reverse recovery energy	E_{rec}	I_{SD} = 100 A, di_s/dt = 1.05 kA/µs (T_{vj} = 175 °C), V_{DD} = 400 V, V_{GS}=-3 V	T_{vj} = 25 °C		0.236		mJ
			T_{vj} = 125 °C		0.452		
			T_{vj} = 175 °C		0.601		

4 IGBT, 3-Level

Table 8 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	650	V
Implemented collector current	I_{CN}			200	A
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_H = 65 °C	90	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		200	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 9 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 100 A, V_{GE} = 15 V	T_{vj} = 25 °C	0.74	1.17	1.59	V
			T_{vj} = 125 °C		1.20		
			T_{vj} = 150 °C		1.21		
Gate threshold voltage	V_{GEth}	I_C = 2 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		3.25	4.0	4.75	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CC} = 400 V, T_{vj} = 25 °C			0.84		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0.0		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			14.3		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.05		nF

(table continues...)

Table 9 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter cut-off current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			1	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 100 A, V_{CC} = 400 V, V_{GE} = ±15 V, R_{Gon} = 1.3 Ω	T_{vj} = 25 °C		0.046		µs
			T_{vj} = 125 °C		0.046		
			T_{vj} = 150 °C		0.050		
Rise time (inductive load)	t_r	I_C = 100 A, V_{CC} = 400 V, V_{GE} = ±15 V, R_{Gon} = 1.3 Ω	T_{vj} = 25 °C		0.005		µs
			T_{vj} = 125 °C		0.006		
			T_{vj} = 150 °C		0.007		
Turn-off delay time (inductive load)	t_{doff}	I_C = 100 A, V_{CC} = 400 V, V_{GE} = ±15 V, R_{Goff} = 1 Ω	T_{vj} = 25 °C		0.085		µs
			T_{vj} = 125 °C		0.116		
			T_{vj} = 150 °C		0.122		
Fall time (inductive load)	t_f	I_C = 100 A, V_{CC} = 400 V, V_{GE} = ±15 V, R_{Goff} = 1 Ω	T_{vj} = 25 °C		0.037		µs
			T_{vj} = 125 °C		0.054		
			T_{vj} = 150 °C		0.064		
Turn-on energy loss per pulse	E_{on}	I_C = 100 A, V_{CC} = 400 V, L_σ = 15 nH, V_{GE} = ±15 V, R_{Gon} = 1.3 Ω, di/dt = 1050 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.232		mJ
			T_{vj} = 125 °C		0.387		
			T_{vj} = 150 °C		0.444		
Turn-off energy loss per pulse	E_{off}	I_C = 100 A, V_{CC} = 400 V, L_σ = 15 nH, V_{GE} = ±15 V, R_{Goff} = 1 Ω, dv/dt = 5190 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		1.12		mJ
			T_{vj} = 125 °C		1.8		
			T_{vj} = 150 °C		2.05		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, Valid with IFX pre-applied Thermal Interface Material				0.723	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

5 Diode, 3-Level

Table 10 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	650	V
Implemented forward current	I_{FN}			150	A

(table continues...)

Table 10 (continued) Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Continuous DC forward current	I_F			100	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		200	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	1270	A^2s
			T_{vj} = 150 °C	1480	

Table 11 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 100 A, V_{GE} = 0 V	T_{vj} = 25 °C	0.74	1.35	1.86	V
			T_{vj} = 125 °C		1.29		
			T_{vj} = 150 °C		1.25		
Peak reverse recovery current	I_{RM}	V_{CC} = 400 V, I_F = 100 A, V_{GE} = -3 V, -di$_F$/dt = 4.48 kA/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		80		A
			T_{vj} = 125 °C		118		
			T_{vj} = 150 °C		130		
Recovered charge	Q_r	V_{CC} = 400 V, I_F = 100 A, V_{GE} = -3 V, -di$_F$/dt = 4.48 kA/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3.82		µC
			T_{vj} = 125 °C		6.77		
			T_{vj} = 150 °C		7.68		
Reverse recovery energy	E_{rec}	V_{CC} = 400 V, I_F = 100 A, V_{GE} = -3 V, -di$_F$/dt = 4.48 kA/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.694		mJ
			T_{vj} = 125 °C		1.56		
			T_{vj} = 150 °C		1.88		
Thermal resistance, junction to heat sink	R_{thJH}	per diode, Valid with IFX pre-applied Thermal Interface Material				0.802	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

6 NTC-Thermistor

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2-1/(298{,}15\ K))]$		3375		K

(table continues...)

Table 12 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2-1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2-1/(298{,}15\ K))]$		3433		K

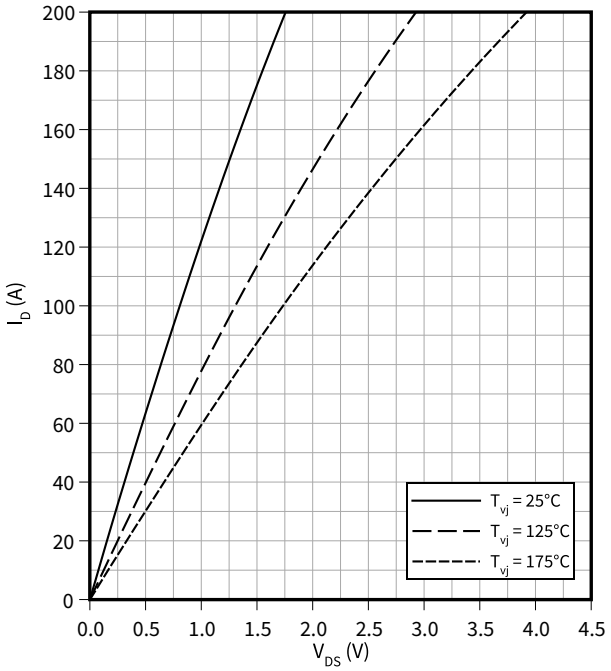
***Note**: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4.*

7 Characteristics diagrams

Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

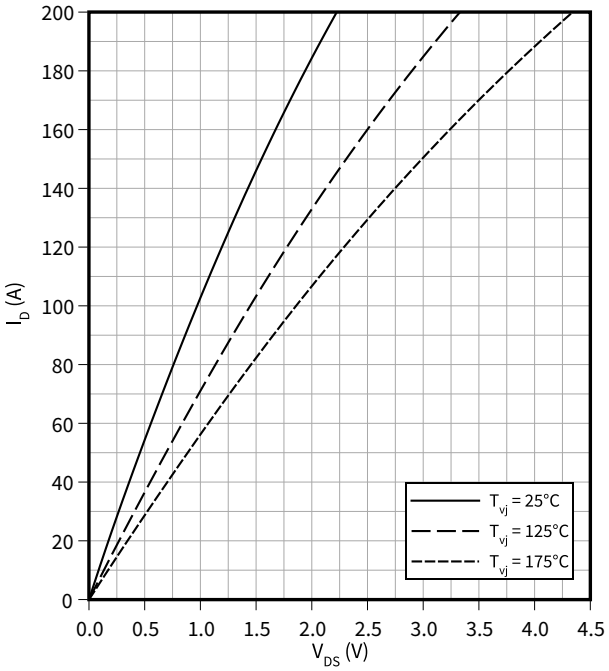
V_{GS} = 18 V



Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

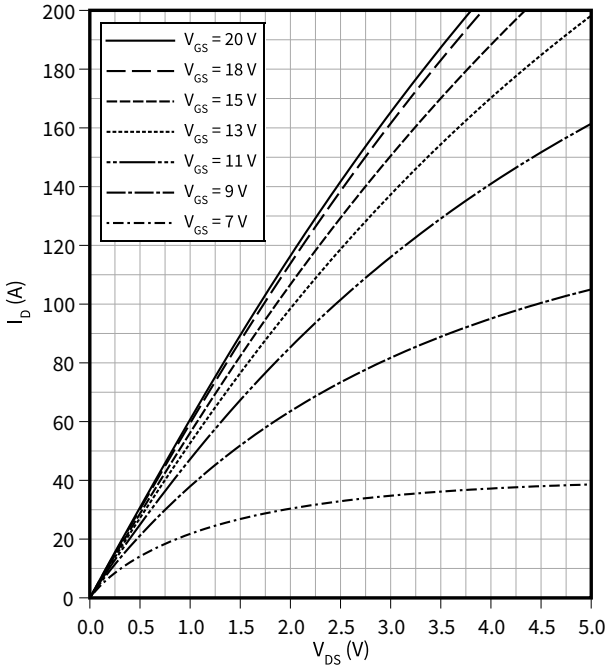
V_{GS} = 15 V



Output characteristic field (typical), MOSFET

$I_D = f(V_{DS})$

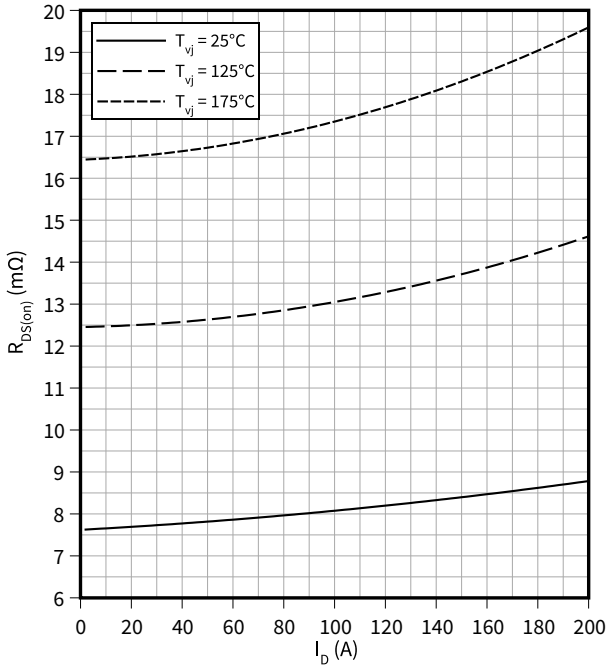
T_{vj} = 175 °C



Drain source on-resistance (typical), MOSFET

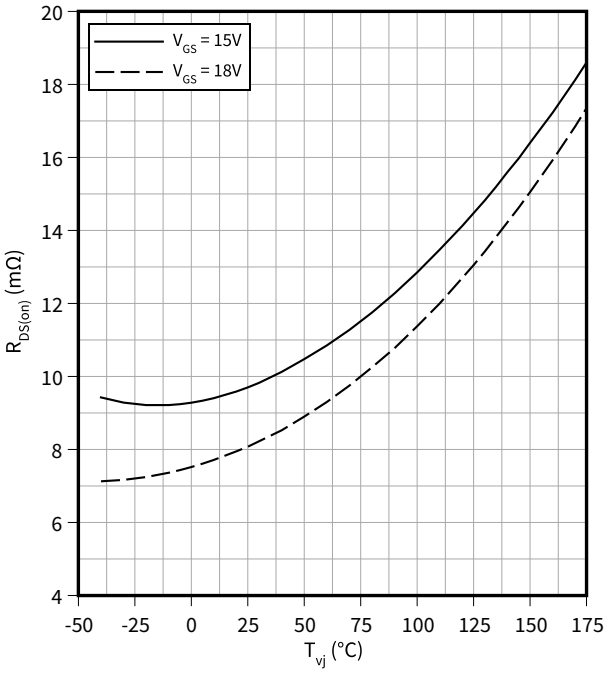
$R_{DS(on)} = f(I_D)$

V_{GS} =18 V



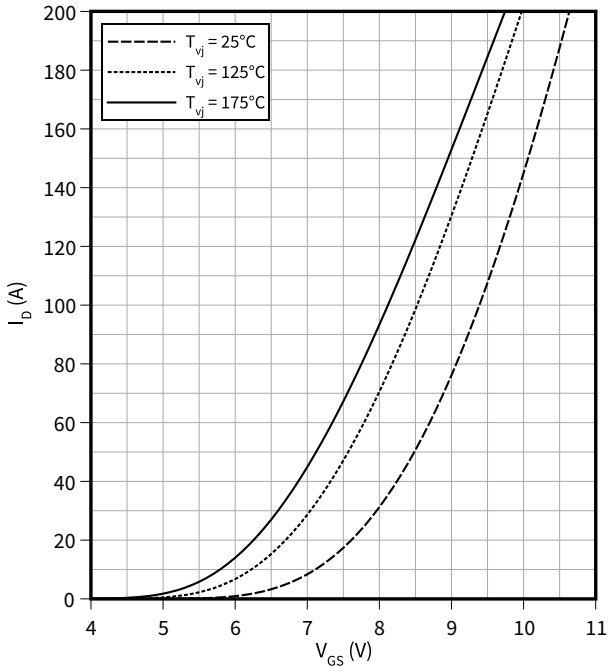
Drain source on-resistance (typical), MOSFET

$R_{DS(on)} = f(T_{vj})$
$I_D = 100$ A



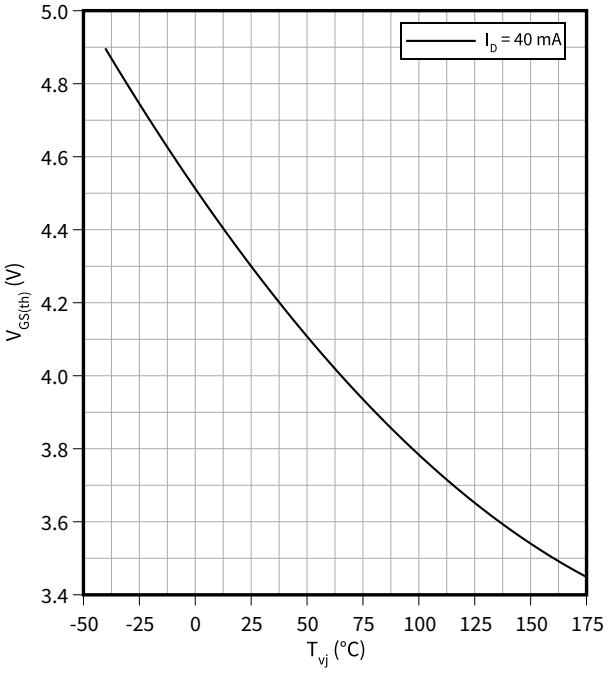
Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$
$V_{DS} = 20$ V



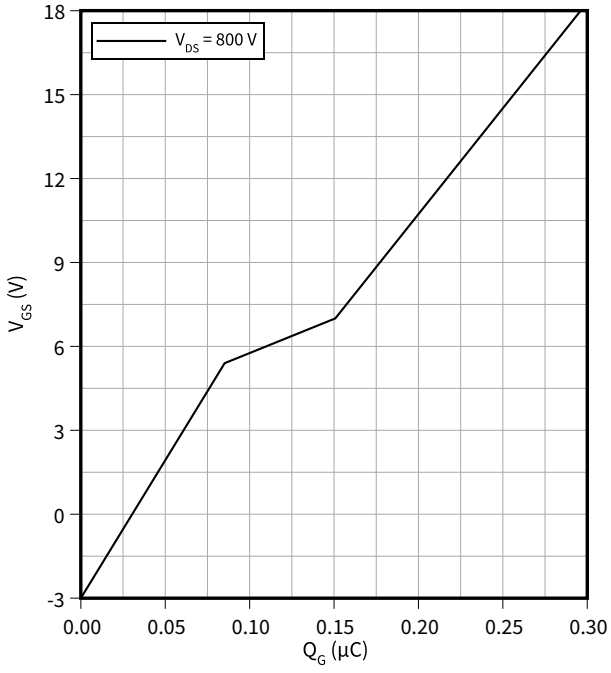
Gate-source threshold voltage (typical), MOSFET

$V_{GS(th)} = f(T_{vj})$
$V_{DS} = V_{GS}$



Gate charge characteristic (typical), MOSFET

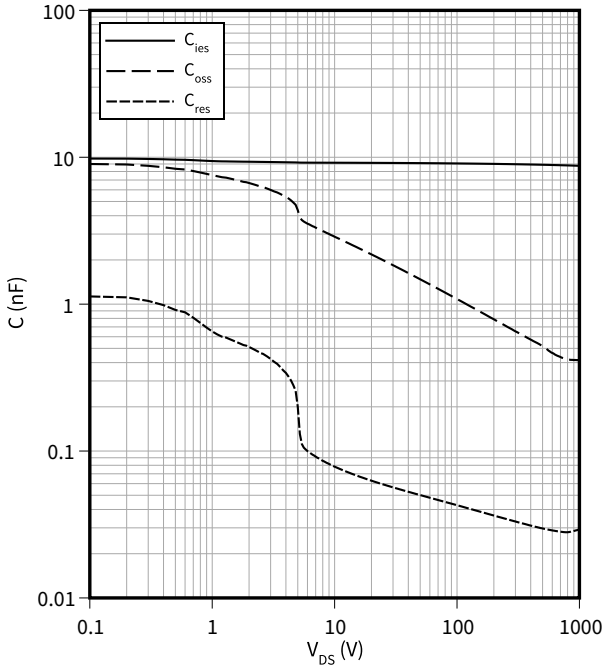
$V_{GS} = f(Q_G)$
$I_D = 100$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET

$C = f(V_{DS})$

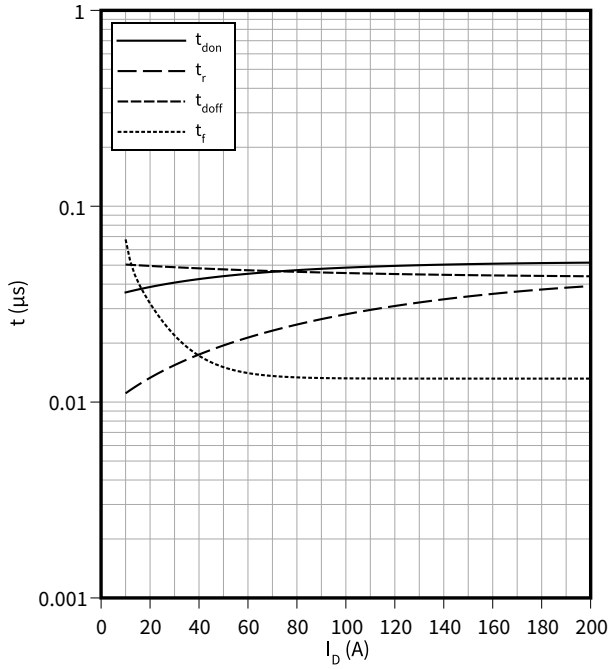
$f = 100\ kHz, T_{vj} = 25\ °C, V_{GS} = 0\ V$



Switching times (typical), MOSFET

$t = f(I_D)$

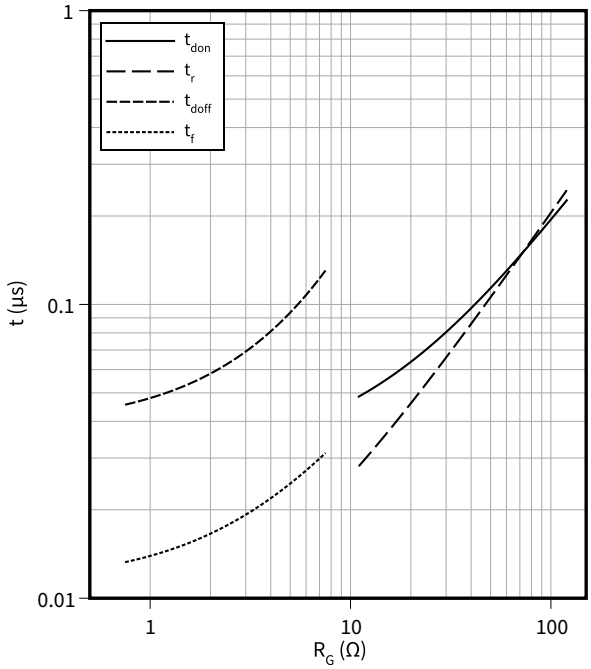
$R_{Goff} = 0.75\ \Omega, R_{Gon} = 11\ \Omega, V_{DD} = 400\ V, T_{vj} = 175\ °C, V_{GS} = -3/18\ V$



Switching times (typical), MOSFET

$t = f(R_G)$

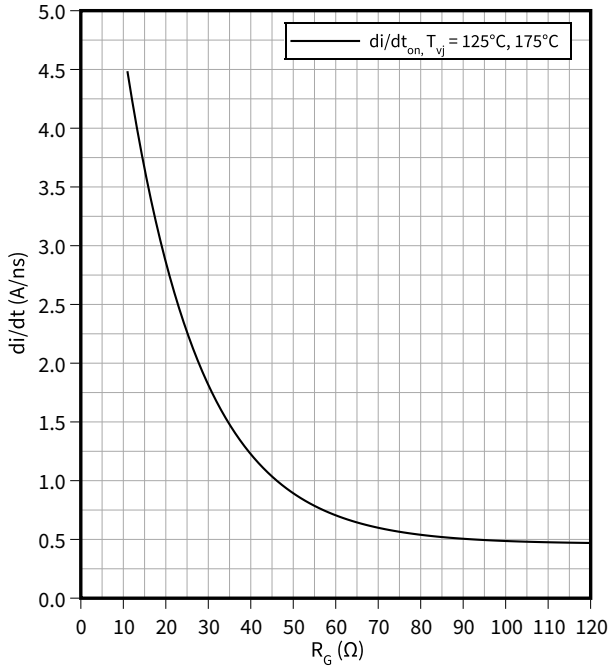
$V_{DD} = 400\ V, I_D = 100\ A, T_{vj} = 175\ °C, V_{GS} = -3/18\ V$



Current slope (typical), MOSFET

$di/dt = f(R_G)$

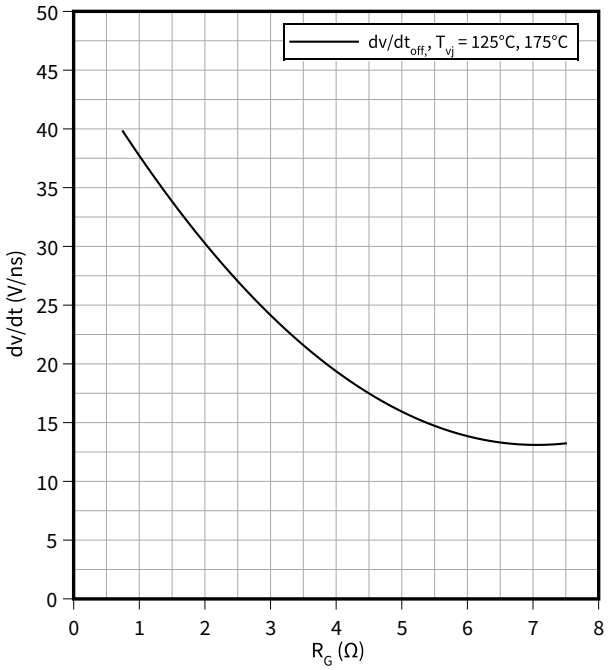
$V_{DD} = 400\ V, I_D = 100\ A, V_{GS} = -3/18\ V$



Voltage slope (typical), MOSFET

$dv/dt = f(R_G)$

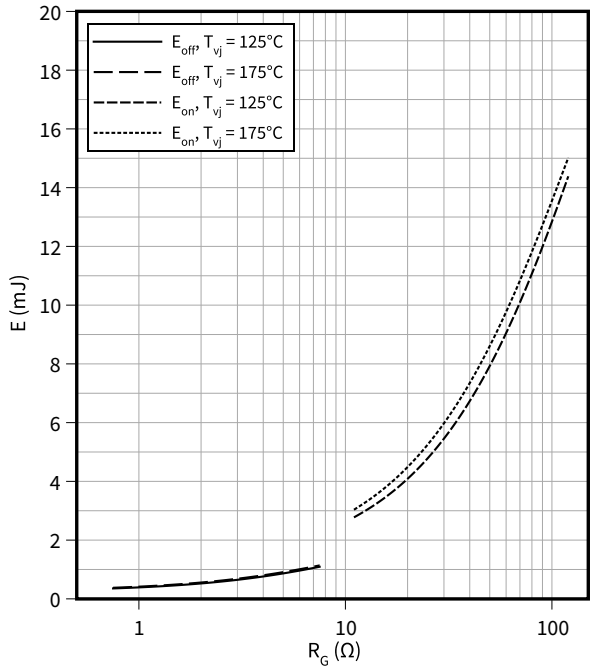
V_{DD} = 400 V, I_D = 100 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET

$E = f(R_G)$

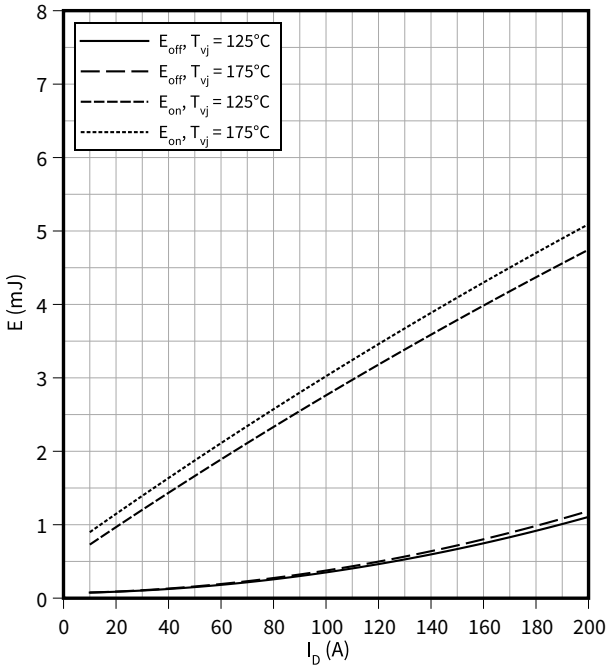
V_{DD} = 400 V, I_D = 100 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET

$E = f(I_D)$

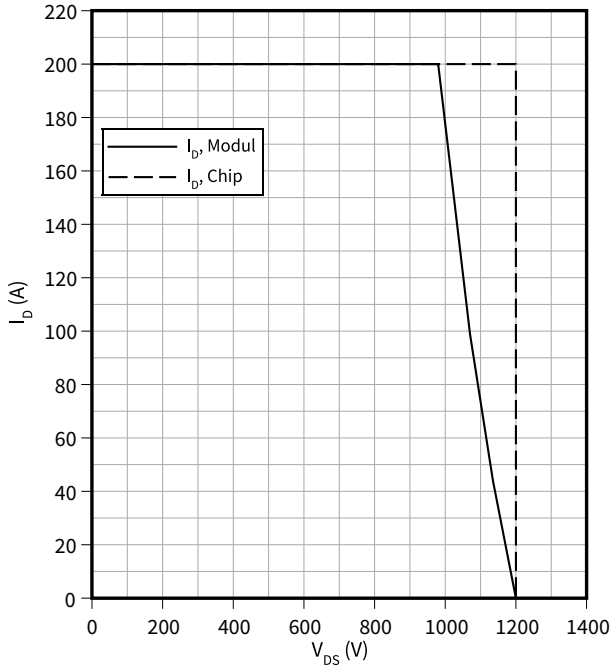
R_{Goff} = 0.75 Ω, R_{Gon} = 11 Ω, V_{DD} = 400 V, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET

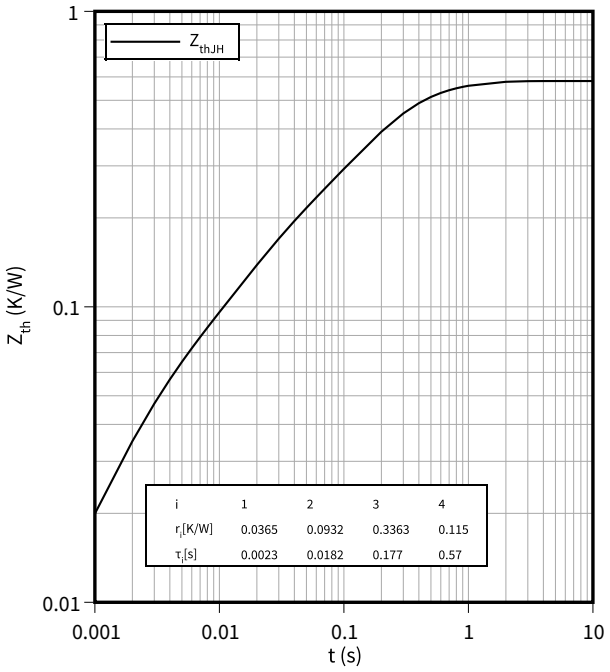
$I_D = f(V_{DS})$

R_{Goff} = 0.75 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Transient thermal impedance, MOSFET

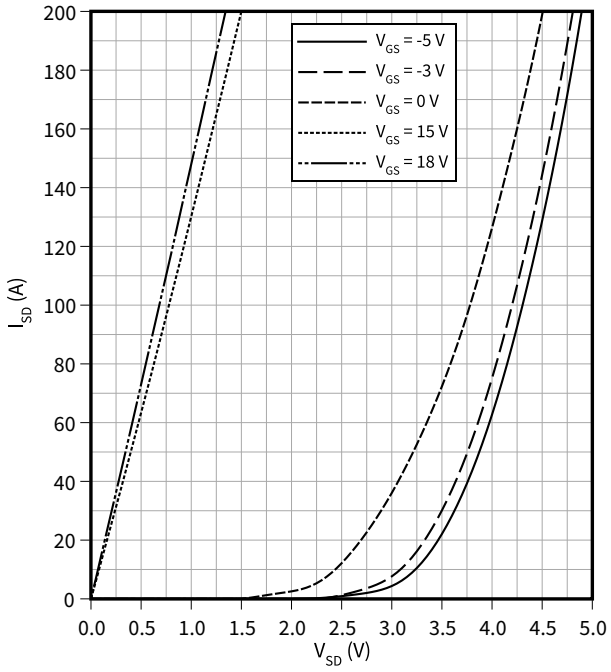
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET

$I_{SD} = f(V_{SD})$

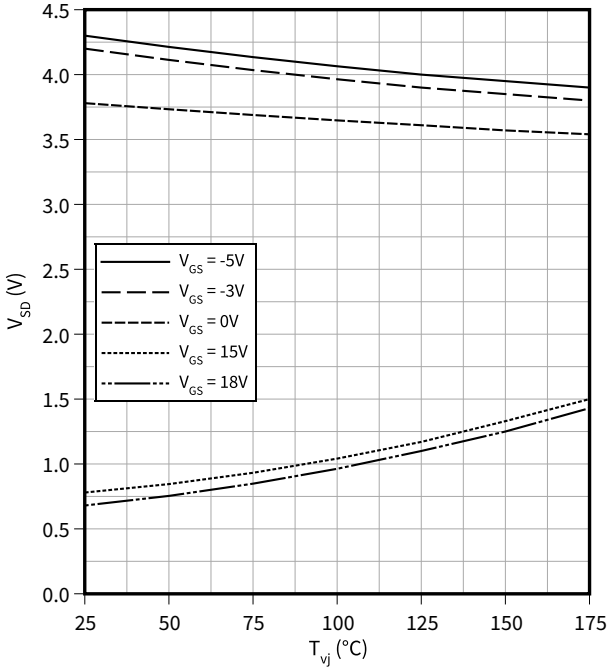
$T_{vj} = 25\ °C$



Forward voltage of body diode (typical), MOSFET

$V_{SD} = f(T_{vj})$

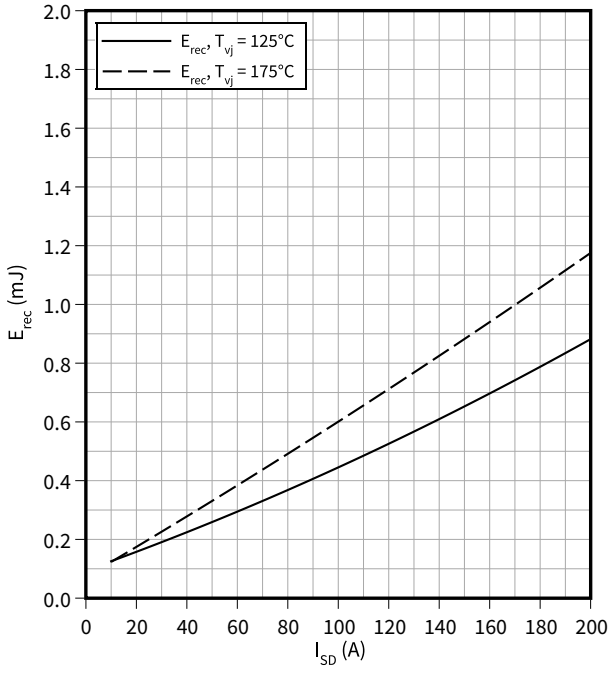
$I_{SD} = 100\ A$



Switching losses body diode (typical), MOSFET

$E_{rec} = f(I_{SD})$

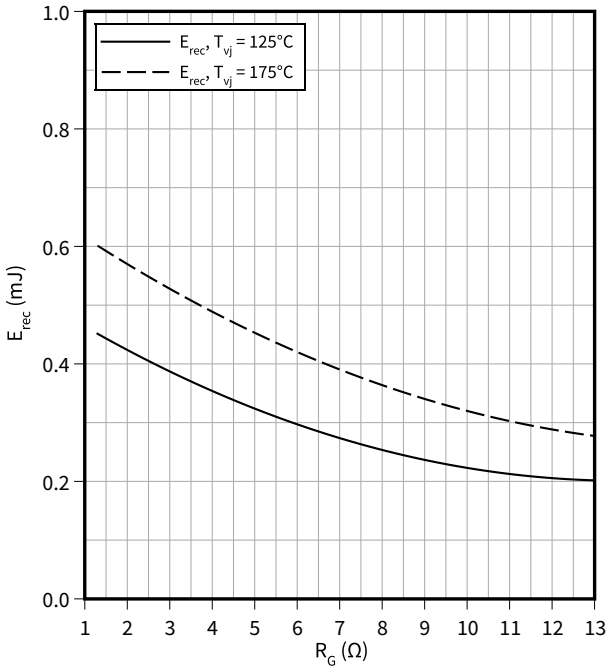
$R_{Gon} = 1.3\ \Omega$, $V_{DD} = 400\ V$



Switching losses body diode (typical), MOSFET

$E_{rec} = f(R_G)$

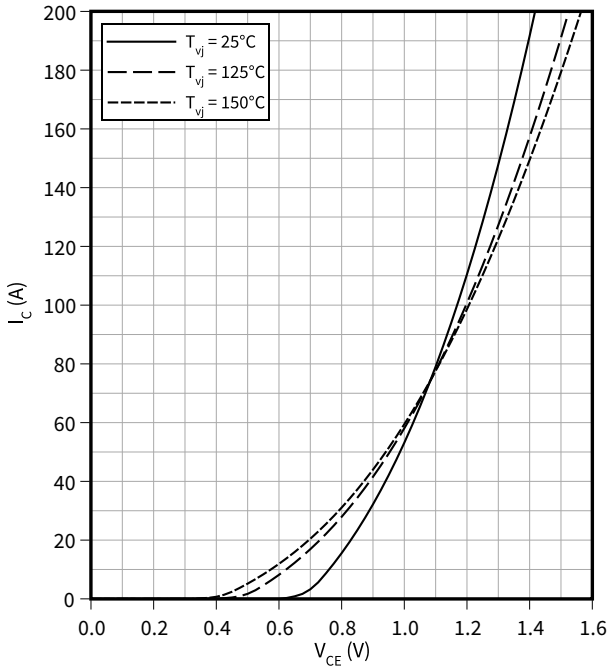
$V_{DD} = 400\ V$, $I_{SD} = 100\ A$



Output characteristic (typical), IGBT, 3-Level

$I_C = f(V_{CE})$

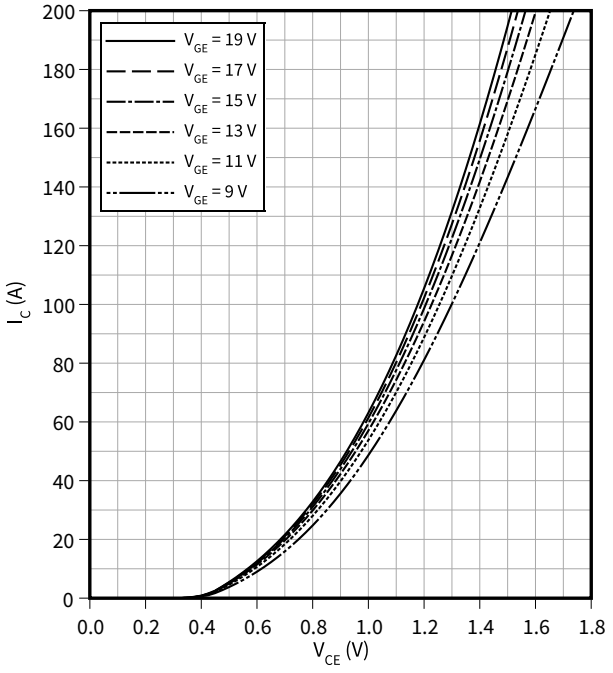
$V_{GE} = 15\ V$



Output characteristic field (typical), IGBT, 3-Level

$I_C = f(V_{CE})$

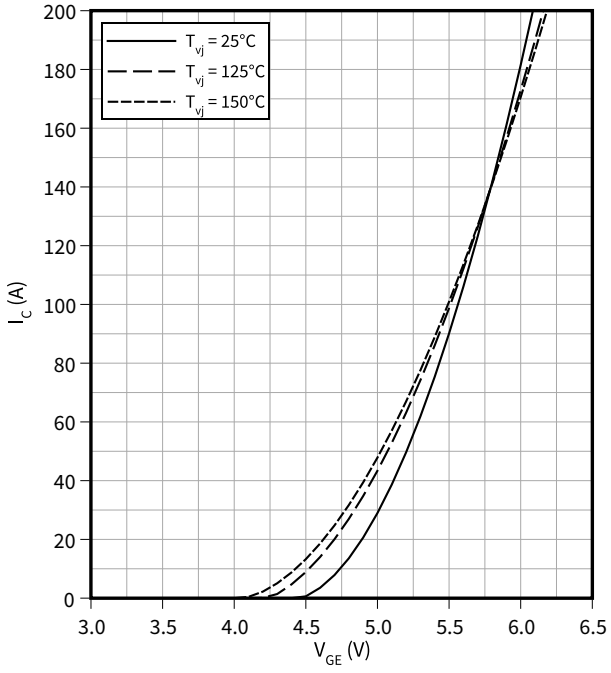
$T_{vj} = 150\ °C$



Transfer characteristic (typical), IGBT, 3-Level

$I_C = f(V_{GE})$

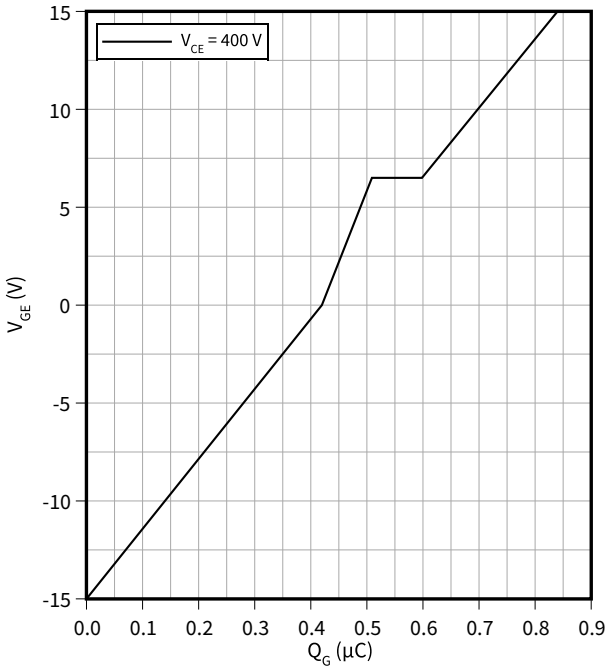
$V_{CE} = 20\ V$



Gate charge characteristic (typical), IGBT, 3-Level

$V_{GE} = f(Q_G)$

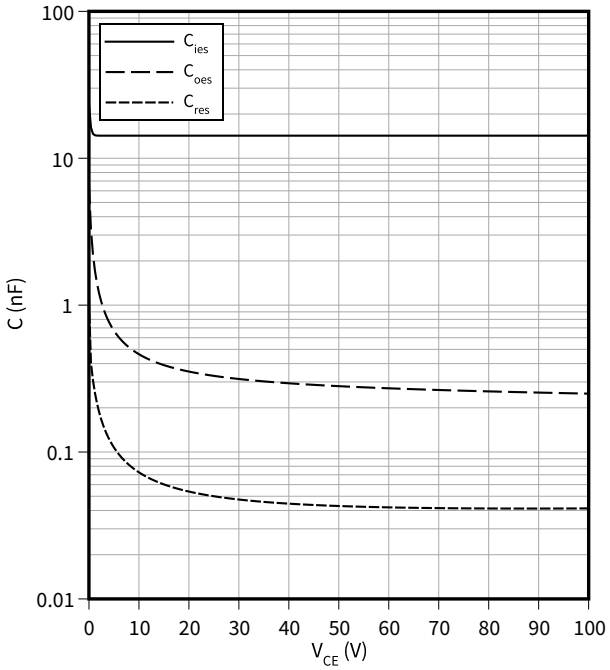
$I_C = 100\ A$, $T_{vj} = 25\ °C$



Capacity characteristic (typical), IGBT, 3-Level

$C = f(V_{CE})$

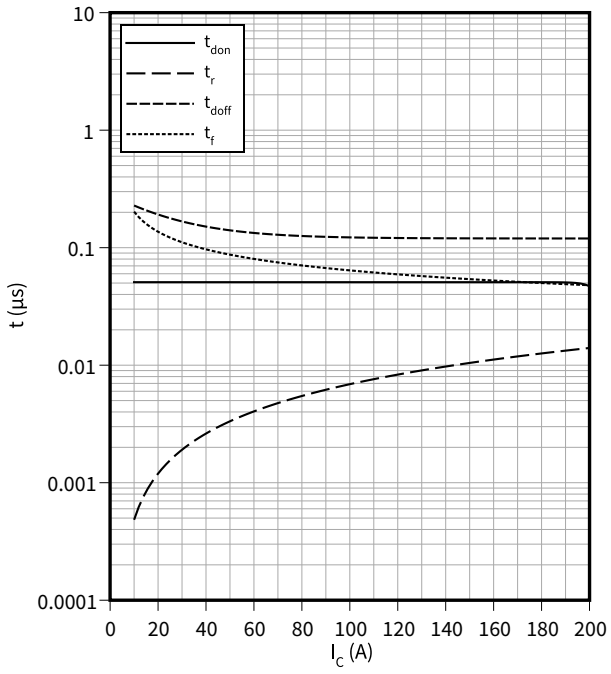
$f = 100\ kHz$, $V_{GE} = 0\ V$, $T_{vj} = 25\ °C$



Switching times (typical), IGBT, 3-Level

$t = f(I_C)$

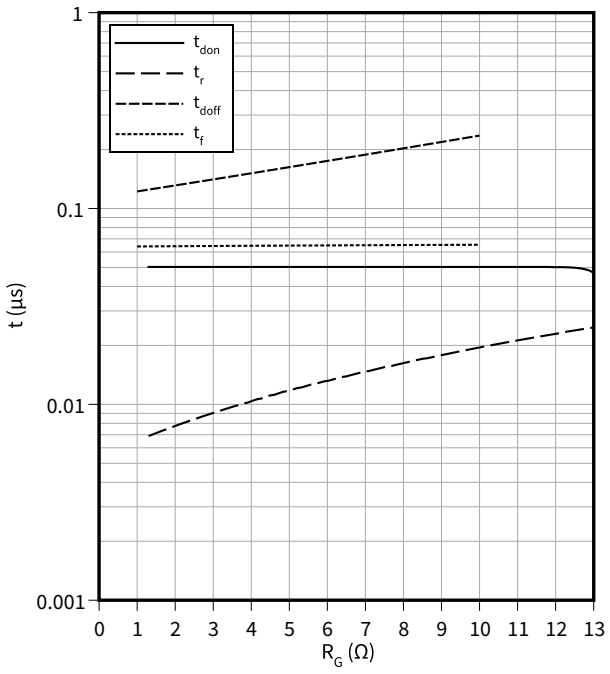
$R_{Goff} = 1\ Ω$, $R_{Gon} = 1.3\ Ω$, $V_{GE} = ±15\ V$, $V_{CC} = 400\ V$, $T_{vj} = 150\ °C$



Switching times (typical), IGBT, 3-Level

$t = f(R_G)$

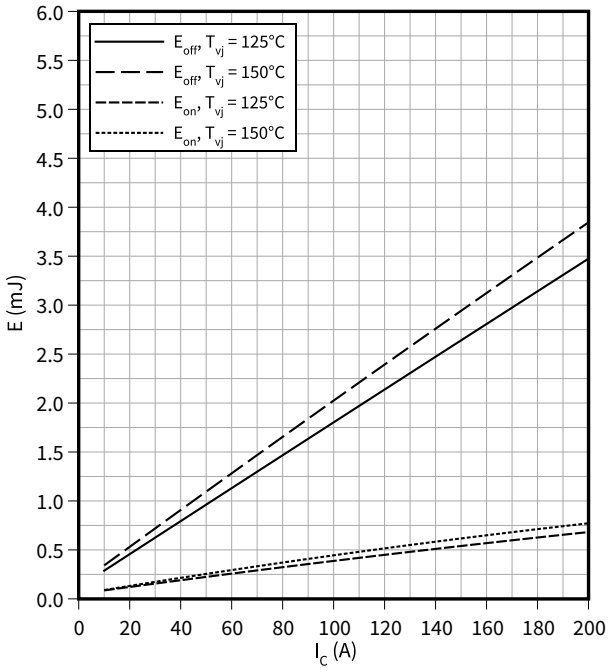
$V_{GE} = ±15\ V$, $I_C = 100\ A$, $V_{CC} = 400\ V$, $T_{vj} = 150\ °C$



Switching losses (typical), IGBT, 3-Level

$E = f(I_C)$

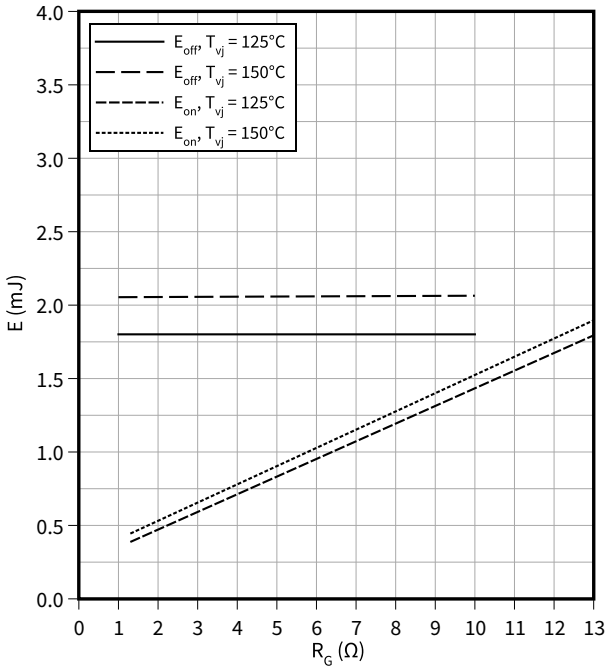
$R_{Goff} = 1\ \Omega$, $R_{Gon} = 1.3\ \Omega$, $V_{GE} = \pm 15$ V, $V_{CC} = 400$ V



Switching losses (typical), IGBT, 3-Level

$E = f(R_G)$

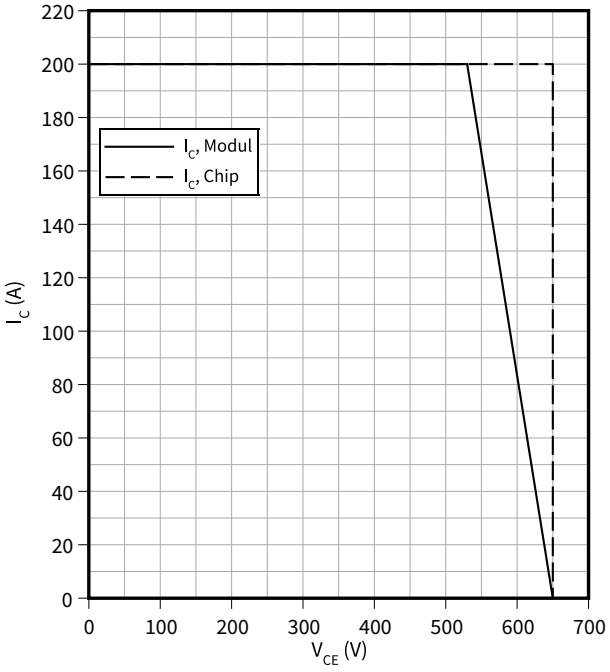
$V_{GE} = \pm 15$ V, $I_C = 100$ A, $V_{CC} = 400$ V



Reverse bias safe operating area (RBSOA), IGBT, 3-Level

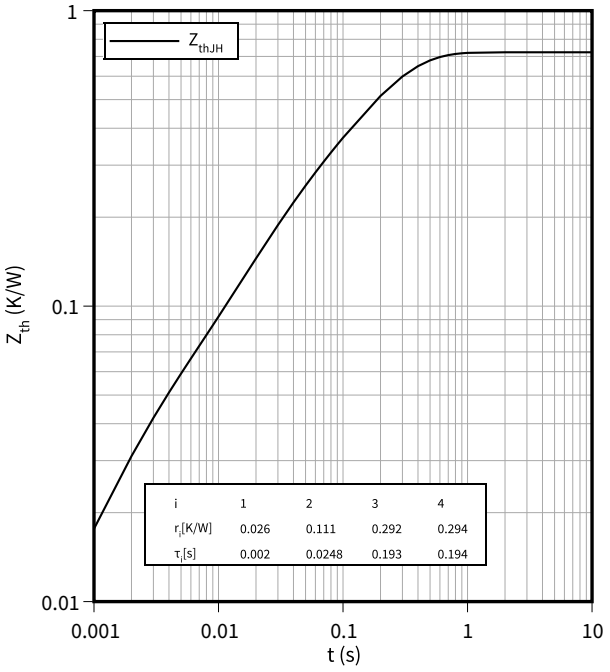
$I_C = f(V_{CE})$

$R_{Goff} = 1\ \Omega$, $V_{GE} = \pm 15$ V, $T_{vj} = 150$ °C



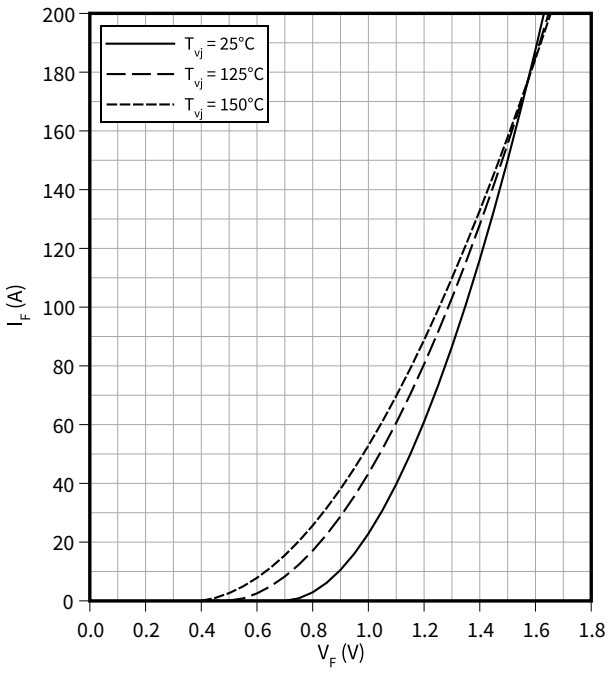
Transient thermal impedance, IGBT, 3-Level

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, 3-Level

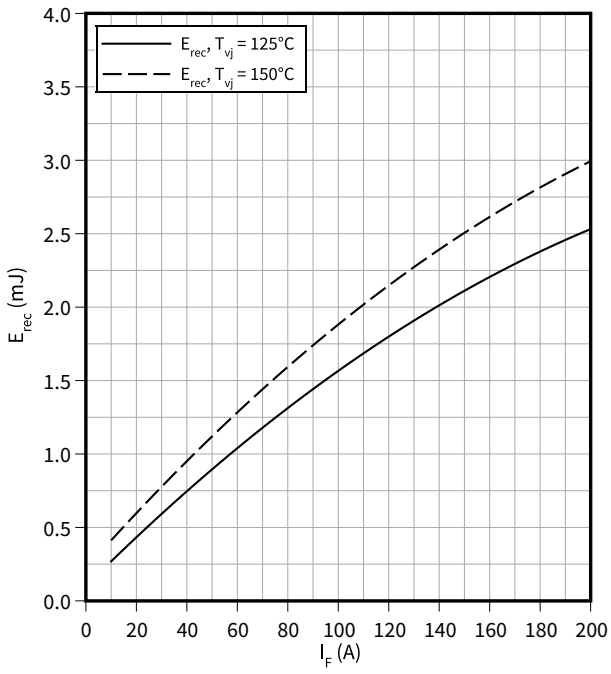
$I_F = f(V_F)$



Switching losses (typical), Diode, 3-Level

$E_{rec} = f(I_F)$

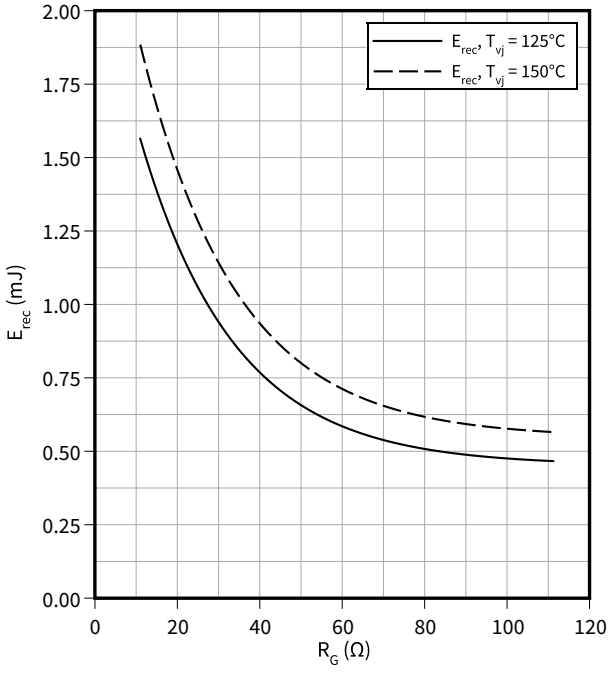
$R_{Gon} = 11\ \Omega$, $V_{CC} = 400\ V$



Switching losses (typical), Diode, 3-Level

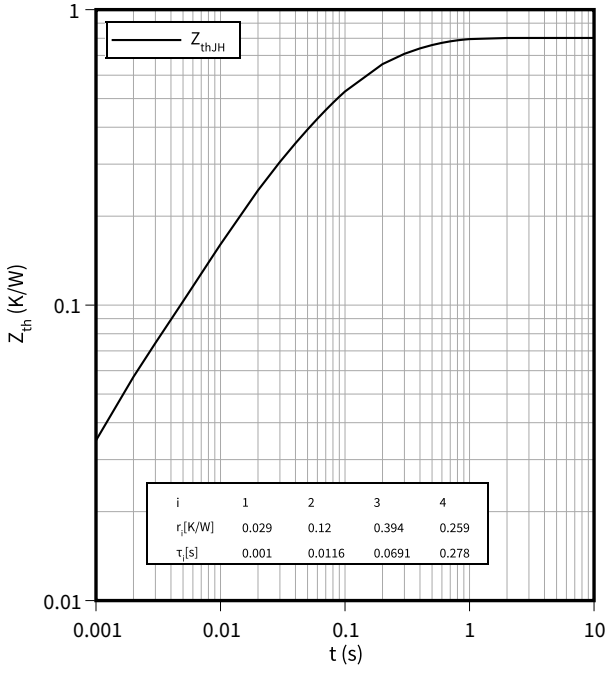
$E_{rec} = f(R_G)$

$I_F = 100\ A$, $V_{CC} = 400\ V$



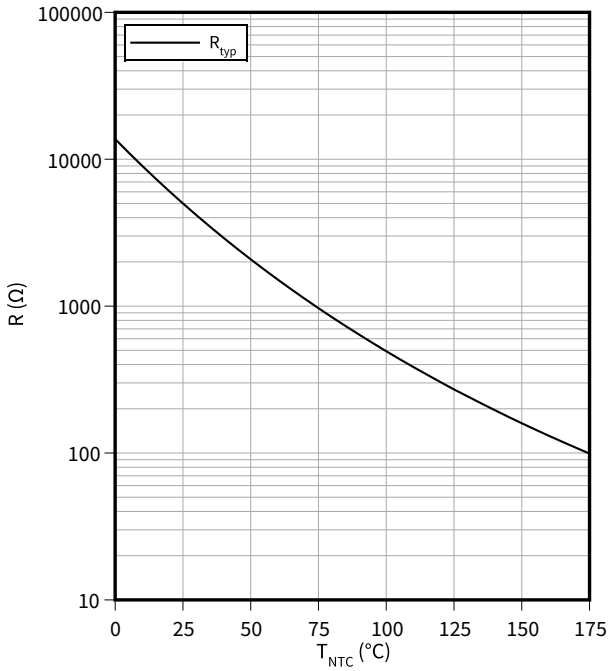
Transient thermal impedance, Diode, 3-Level

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



8 Circuit diagram

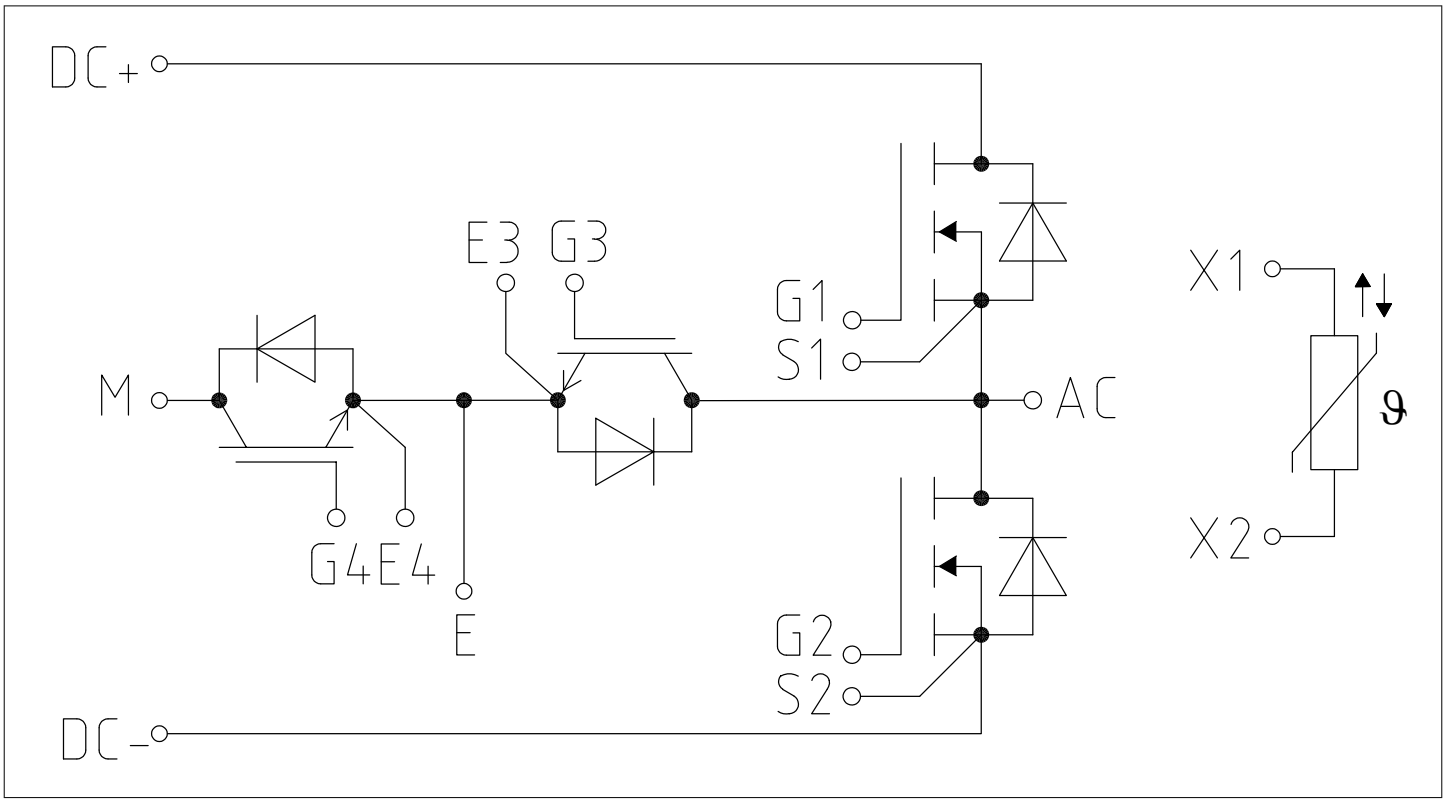


Figure 1

9 Package outlines

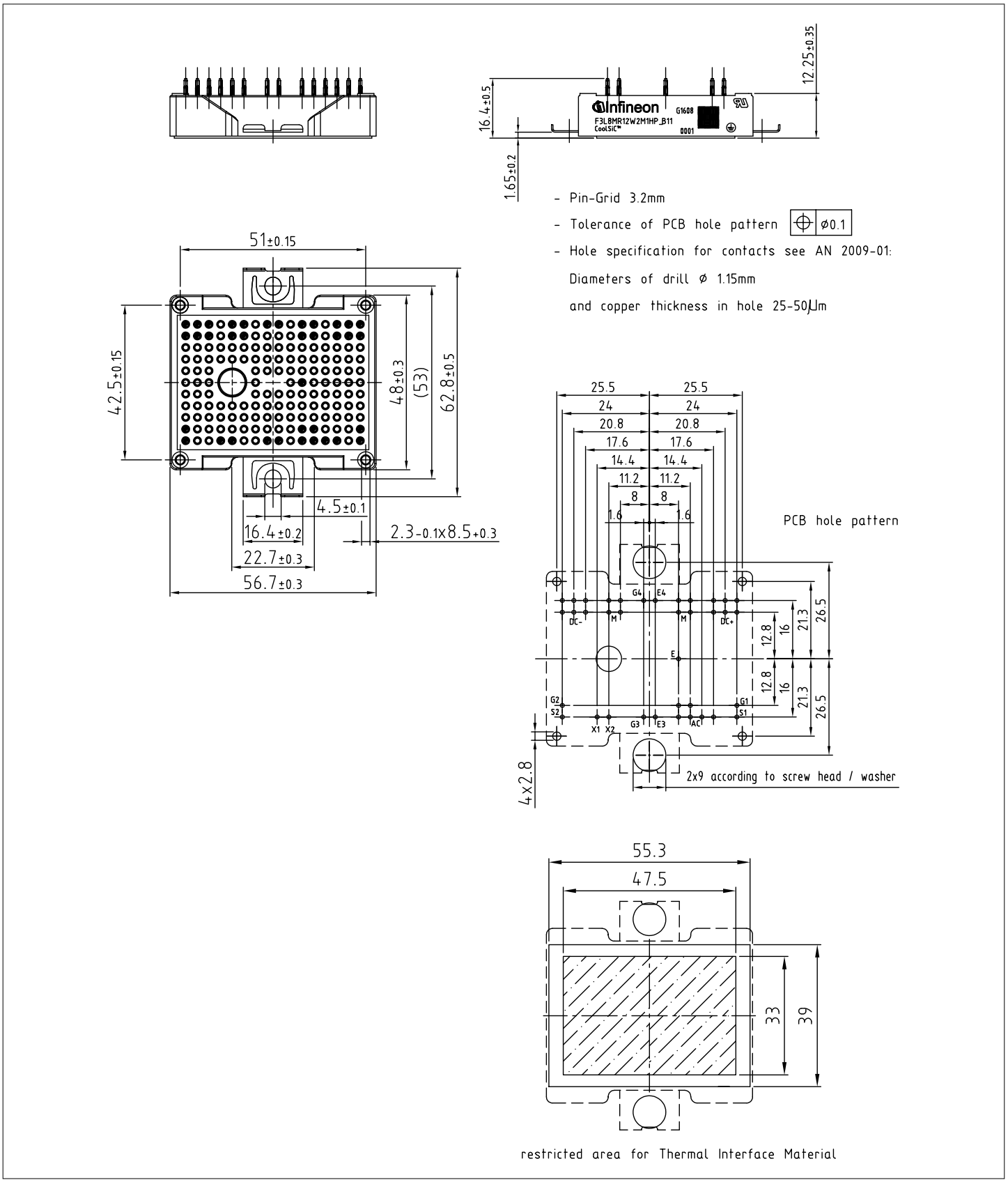


Figure 2

10 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-04-07	
1.00	2022-03-09	Final datasheet
1.10	2022-03-11	Final datasheet
1.20	2025-04-28	Final datasheet

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